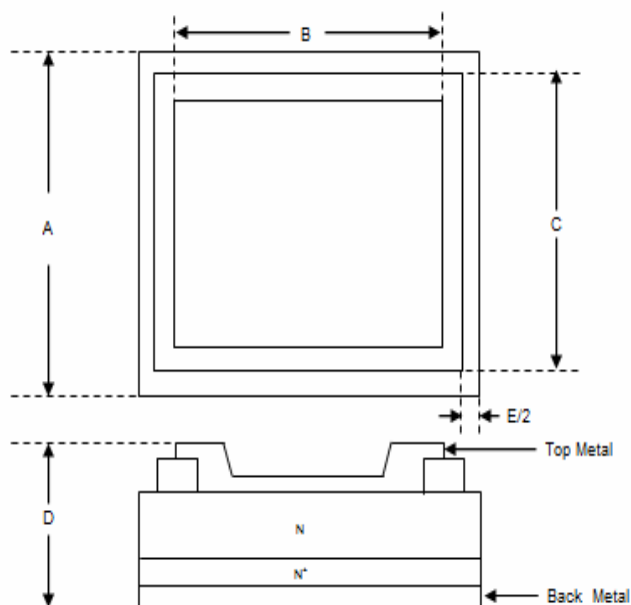


Preliminary

CT58A080HG

Trench Schottky Barrier Diode Wafer (TSBD)



Item	Dimensions	
	um	mil
Die Size (A)	1512	58
Top Metal Pad Size (B)	1260	49.6
Passivation Seal (C)	1442	56.8
Wafer Thickness (D)	260	10.2
Scribe Line Width (E)	70	2.76
Other Informations		
Wafer Size	6"	
Gross Die	7110	
Top Metal	Ag	
Back Metal	Ag	

Electrical Characteristics @TA=25°C

Item	Symbol	Spec. Limit	Die Sort	Unit
Maximum Repetitive Peak Reverse Voltage @0.1mA	V_{RRM}	80	85	V
Maximum Average Forward Rectified Current	I_O	5	-	A
Forward Voltage Drop, @ $I_F=3A$ @ $I_F=5A$	V_F	0.56 0.66	0.55 -	V
Maximum Reverse Current at Rated V_{RRM}	I_R	40	20	μA
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	80	-	A
Operating Temperature Range	T_J	-50 to +150	-	°C
Storage Temperature Range	T_{STG}	-50 to +150	-	°C